

PI3WVR626

2:1 MIPI 2-Data Lane Switch

Description

The DIODES PI3WVR626 is a two-data-lane MIPI switch. This 6 channel single-pole, double-throw (SPDT) switch is optimized for switching between two high-speed (HS) or low-power (LP) MIPI signal. The PI3WVR626 is designed for the MIPI specification and allows connection to CSI/DSI, C-PHY/D-PHY module.

Application(s)

- Cellular Phones, Smart Phones
- Tablets
- Laptops
- Displays

Features

- 3-lane, 2:1 Switches that support D-PHY and C-PHY
- Data Rate Support: up to 3.5Gbps C-PHY, up to 4.5Gb/s D-PHY.
- Bandwidth: 6GHz Typical
- Low Crosstalk: -35 dB@1.25 GHz
- Input Signals 0 to 1.3V
- R_{ON} : 5.0 Ω Typical LP & HS MIPI
- ΔR_{ON} : 0.2 Ω Typical LP & HS MIPI
- R_{ON_FLAT} : 0.1 Ω Typical LP & HS MIPI
- I_{CC} : 11 μ A Typical
- Skew of Opposite Transitions of the Same Output: 5ps Typical
- V_{DD} Operating Range: 1.5V to 3.6V
- ESD Tolerance: 2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.
<https://www.diodes.com/quality/product-definitions/>
- Packaging (Pb-free & Green):
 - 24-Pin, X1QFN (2.5mm x 2.5mm) (XEB)

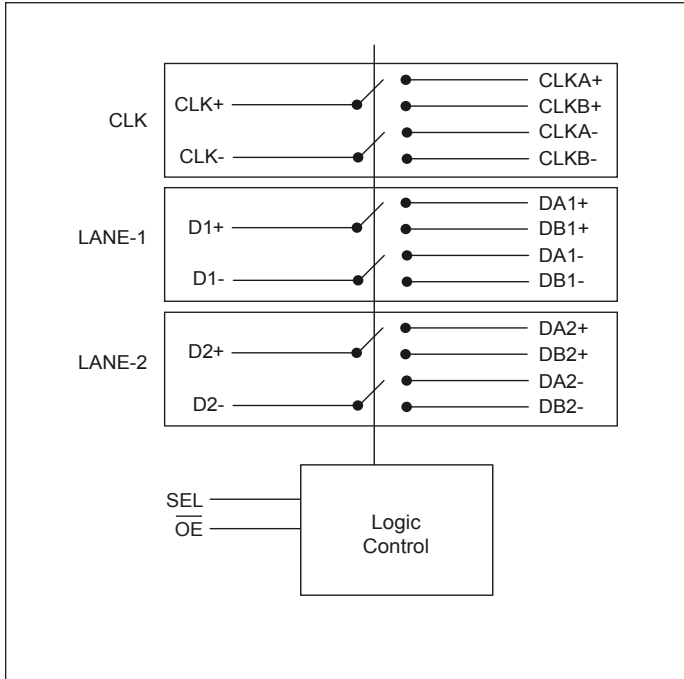
Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

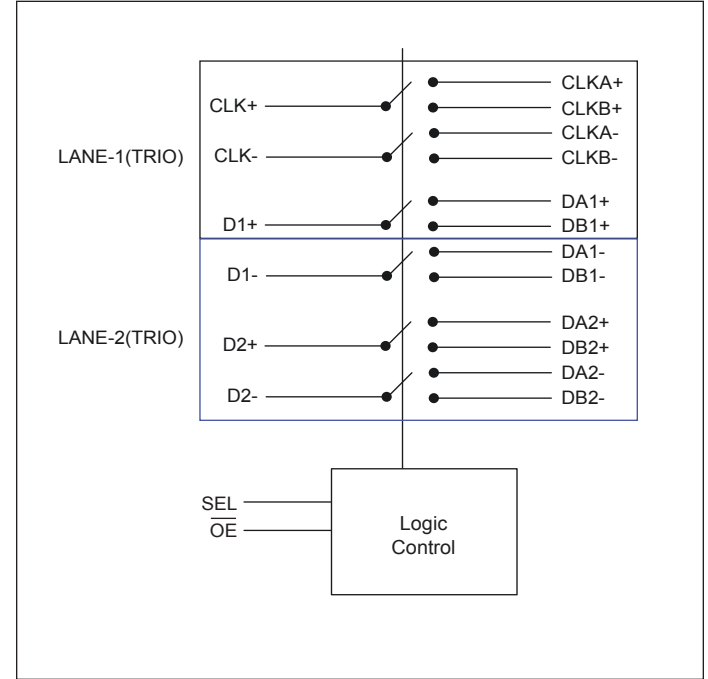
PI3WVR626

Block Diagram

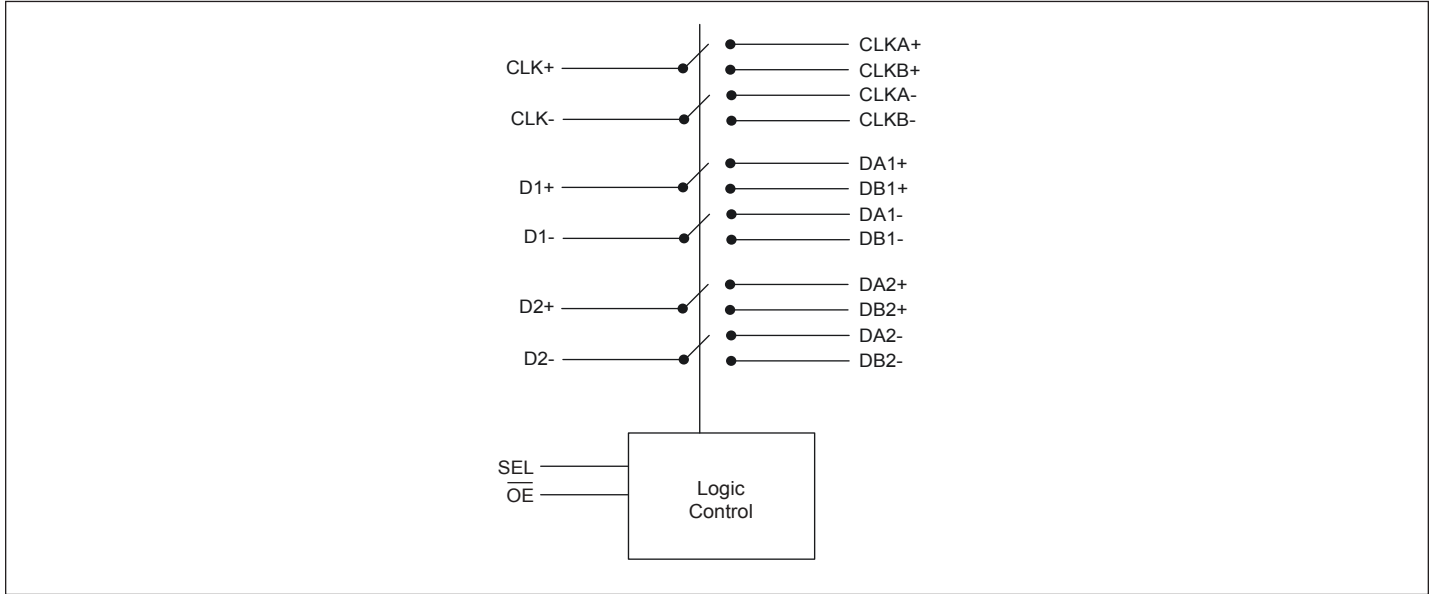
PI3WVR626 D-PHY Application



PI3WVR626 C-PHY Application



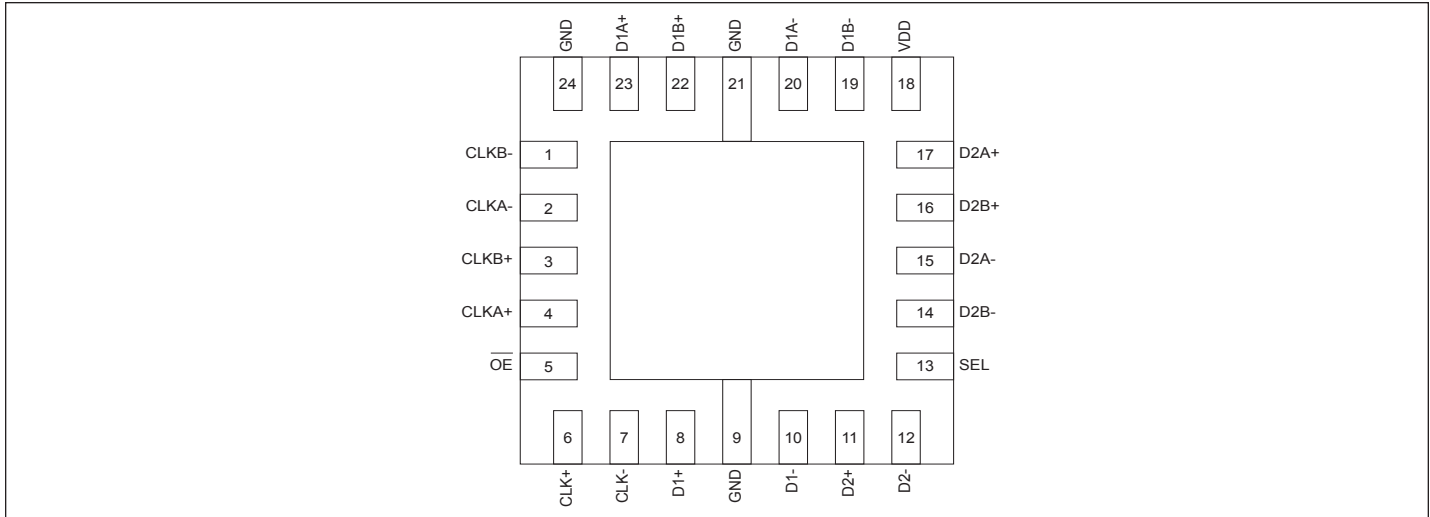
Block Diagram



Truth Table

| SEL | $\overline{\text{OE}}$ | Function |
|------|------------------------|--|
| LOW | LOW | CLK+ = CLKA+, CLK- = CLKA-, Dn(+/-) = DAn(+/-) |
| HIGH | LOW | CLK+ = CLKB+, CLK- = CLKB-, Dn(+/-) = DBn(+/-) |
| X | HIGH | Clock and Data Ports High Impedance |

Pin Configuration



Pin Description

| Pin# | Pin Name | Type | Description |
|-----------|-----------------|--------|---|
| 18 | V _{DD} | Power | 1.5V to 3.3V power supply |
| 9, 21, 24 | GND | Ground | Ground |
| 5 | \overline{OE} | I | Output enable. if OE is low, IC is enabled. if OE is high, IC is power down and all I/Os are Hi-Z |
| 13 | SEL | I | Switch logic control |
| 14 | D2B- | I/O | Negative differential signal 2 for port B |
| 16 | D2B+ | I/O | Positive differential signal 2 for port B |
| 15 | D2A- | I/O | Negative differential signal 2 for port A |
| 17 | D2A+ | I/O | Positive differential signal 2 for port A |
| 12 | D2- | I/O | Negative differential signal 2 for COM port |
| 11 | D2+ | I/O | Positive differential signal 2 for COM port |
| 19 | D1B- | I/O | Negative differential signal 1 for port B |
| 22 | D1B+ | I/O | Positive differential signal 1 for port B |
| 20 | D1A- | I/O | Negative differential signal 1 for port A |
| 23 | D1A+ | I/O | Positive differential signal 1 for port A |
| 10 | D1- | I/O | Negative differential signal 1 for COM port |
| 8 | D1+ | I/O | Positive differential signal 1 for COM port |
| 1 | CLKB- | I/O | Clock negative differential signal for port B |
| 3 | CLKB+ | I/O | Clock positive differential signal for port B |
| 2 | CLKA- | I/O | Clock negative differential signal for port A |
| 4 | CLKA+ | I/O | Clock positive differential signal for port A |
| 7 | CLK- | I/O | Clock negative differential signal for COM port |
| 6 | CLK+ | I/O | Clock positive differential signal for COM port |

Absolute Maximum Ratings

Above which useful life may be impaired. For user guidelines, not tested.

| | |
|--|-------------------|
| V_{CC} , Supply Voltage, | -0.5V to 4.5V |
| V_{CNTRL} , DC Input Voltage (\overline{OE} , SEL) ⁽¹⁾ | -0.5V to V_{CC} |
| V_{SW} , DC Switch I/O Voltage ^(1,2) | -0.3V to 2.5V |
| I_{IK} , DC Input Diodes Current | -50mA |
| I_{OUT} , DC Output Current | 25mA |
| T_{STG} , Storage Temperature | -65°C to +150°C |
| T_j , Junction Temperature | 125°C |
| ESD: | |
| Human Body Model, JEDEC: JESD22-A114, All Pins..... | 2.0kV |
| Charged Device Model, JEDEC: JESD22-C101..... | 1.0kV |

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Note:

1. The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.
2. V_{SW} refers to analog data switch paths.

Recommended Operating Conditions

The Recommended operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications.

| Symbol | Description | Test Conditions | Min. | Max. | Units |
|-------------|--|-----------------|------|----------|-------|
| V_{CC} | Supply Voltage | | 1.5 | 3.6 | V |
| V_{CNTRL} | Control Input Voltage (SEL, \overline{OE}) ⁽¹⁾ | | 0 | V_{CC} | V |
| V_{SW} | Switch I/O Voltage (CLK-, D-, CLKA-, CLKB-, DA-, DB-) | HS Mode | 0 | 0.5 | V |
| | | LP Mode | 0 | 1.3 | V |
| T_A | Operating Temperature | | -40 | +85 | °C |

Note:

1. The control inputs must be held HIGH or LOW; they must not float.

DC and Transient Characteristics

All typical values are at $T_A = 25^\circ\text{C}$ unless otherwise specified.

| Symbol | Description | Test Conditions | V_{CC} (V) | $T_A = -40^\circ\text{C to } +85^\circ\text{C}$ | | | Units |
|--------------------------------|---|--|--------------|---|------|------|---------------|
| | | | | Min. | Typ. | Max. | |
| V_{IK} | Clamp Diode Voltage (\overline{OE} , SEL) | $I_{IN} = -18\text{mA}$ | 1.5 | -1.2 | | -0.6 | V |
| V_{IH} | Input Voltage High | SEL, \overline{OE} | 1.5 to 3.3 | 1.0 | | | V |
| V_{IL} | Input Voltage Low | SEL, \overline{OE} | 1.5 to 3.3 | | | 0.5 | V |
| I_{IN} | Control Input Leakage (\overline{OE} , SEL) | $V_{CNTRL} = 0 \text{ to } V_{CC}$ | 3.3 | -1.0 | | 1.0 | μA |
| $I_{NO(OFF)}$ $I_{NC(OFF)}$ | Off Leakage Current of Port CLKA-, DA-, CLKB- and DB- | $V_{SW} = 0.0 \leq \text{DATA} \leq 1.3\text{V}$ | 3.3 | -1.0 | | 1.0 | μA |
| $I_{A(ON)}$ | On Leakage Current of Common Ports (CLK-, D-) | $V_{SW} = 0.0 \leq \text{DATA} \leq 1.3\text{V}$ | 3.3 | -1.0 | | 1.0 | μA |
| I_{OFF} | Power-Off Leakage Current (All I/O Ports) | $V_{SW} = 0.0 \text{ or } 1.3\text{V}$ | 0 | -5 | | 5.0 | μA |

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| Symbol | Description | Test Conditions | V _{CC} (V) | T _A = -40°C to +85°C | | | Units |
|------------------------------|--|---|---------------------|---------------------------------|------|------|-------|
| | | | | Min. | Typ. | Max. | |
| I _{OZ} | Off-State Leakage | $\frac{V_{SW}}{OE} = 0.0 \leq DATA \leq 1.3V$, $\overline{OE} = High$ | 3.6 | -5 | | 5.0 | μA |
| R _{ON_MIPI_HS} | Switch On Resistance for HS MIPI | I _{ON} = -8mA, $\overline{OE} = 0V$, SEL = V _{CC} or 0V, CLKA, CLKB, DB- or DA- = 0.2V | 1.5 | | 5 | | Ω |
| | | | 2.5 | | | | |
| | | | 3.3 | | | | |
| R _{ON_MIPI_LP} | Switch On Resistance for LP MIPI | I _{ON} = -8mA, $\overline{OE} = 0V$, SEL = V _{CC} or 0V, CLKA, CLKB, DB- or DA- = 1.2V | 1.5 | | 5 | | Ω |
| | | | 2.5 | | | | |
| | | | 3.3 | | | | |
| ΔR _{ON_MIPI_HS} | On Resistance Matching Between HS MIPI Channels ⁽¹⁾ | I _{ON} = -8mA, $\overline{OE} = 0V$, SEL = V _{CC} or 0V, CLKA, CLKB, DB- or DA- = 0.2V | 1.5 | | 0.2 | | Ω |
| | | | 2.5 | | | | |
| | | | 3.3 | | | | |
| ΔR _{ON_MIPI_LP} | On Resistance Matching Between LP MIPI Channels ⁽¹⁾ | I _{ON} = -8mA, $\overline{OE} = 0V$, SEL = V _{CC} or 0V, CLKA, CLKB, DB- or DA- = 1.2V | 1.5 | | 0.2 | | Ω |
| | | | 2.5 | | | | |
| | | | 3.3 | | | | |
| R _{ON_FLAT_MIPI_HS} | On Resistance Flatness for HS MIPI | I _{ON} = -8mA, $\overline{OE} = 0V$, SEL = V _{CC} or 0V, CLKA, CLKB, DB- or DA- = 0 to 0.5V | 1.5 | | 0.1 | | Ω |
| | | | 2.5 | | | | |
| | | | 3.3 | | | | |
| R _{ON_FLAT_MIPI_LP} | On Resistance Flatness for LP MIPI | I _{ON} = -8mA, $\overline{OE} = 0V$, SEL = V _{CC} or 0V, CLKA, CLKB, DB- or DA- = 0 to 1.3V | 1.5 | | 0.1 | | Ω |
| | | | 2.5 | | | | |
| | | | 3.3 | | | | |
| I _{CC} | Quiescent Supply Current | $\frac{V_{SEL}}{OE} = 0$ or V _{CC} , I _{OUT} = 0, $\overline{OE} = 0V$ | 3.6 | | 11 | 20 | μA |
| I _{CCZ} | Quiescent Supply Current (High Impedance) | $\frac{V_{SEL}}{OE} = 0$ or V _{CC} , I _{OUT} = 0, $\overline{OE} = 0V$ | 3.6 | | | 1 | μA |
| I _{CCT} | Increase in I _{CC} Current Per Control Voltage and V _{CC} | V _{SEL} = 0 or V _{CC} , $\overline{OE} =$ 1.5V | 3.6 | | 1 | | μA |

AC Electrical Characteristics

All typical values are for $V_{CC} = 3.3V$ and $T_A = 25^\circ C$ unless otherwise specified.

| Symbol | Description | Test Conditions | V_{CC} (V) | $T_A = -40^\circ C$ to $+85^\circ C$ | | | Units |
|------------|---|--|--------------|--------------------------------------|------|------|---------|
| | | | | Min. | Typ. | Max. | |
| t_{INIT} | Initialization Time V_{CC} to Output ⁽¹⁾ | $R_L = 50\Omega$, $C_L = 0pF$, $V_{SW} = 0.6V$ | 1.5 to 3.6 | | 60 | | μs |
| t_{EN} | Enable Time \overline{OE} to Output | $R_L = 50\Omega$, $C_L = 0pF$, $V_{SW} = 0.6V$ | 1.5 to 3.6 | | 60 | 150 | μs |
| t_{DIS} | Disable Time \overline{OE} to Output | $R_L = 50\Omega$, $C_L = 0pF$, $V_{SW} = 0.6V$ | 1.5 to 3.6 | | 35 | 250 | ns |
| t_{ON} | Turn-On Time SEL to Output | $R_L = 50\Omega$, $C_L = 0pF$, $V_{SW} = 0.6V$ | 1.5 to 3.6 | | 350 | 1100 | ns |
| t_{OFF} | Turn-Off Time SEL to Output | $R_L = 50\Omega$, $C_L = 0pF$, $V_{SW} = 0.6V$ | 1.5 to 3.6 | | 125 | 800 | ns |
| t_{BBM} | Break-Before-Make Time | $R_L = 50\Omega$, $C_L = 0pF$, $V_{SW} = 0.6V$ | 1.5 to 3.6 | | | 450 | ns |
| t_{PD} | Propagation Delay ⁽¹⁾ | $C_L = 0pF$, $R_L = 50\Omega$ | 1.5 to 3.6 | | | 0.25 | ns |
| O_{IRR} | Off Isolation for MIPI ⁽¹⁾ | $R_L = 50\Omega$, $f = 1250MHz$, $\overline{OE} = HIGH$, $V_{SW} = 0.5V$ | 1.5 to 3.6 | | -28 | | dB |
| X_{TALK} | Crosstalk for MIPI ⁽¹⁾ | $R_L = 50\Omega$, $f = 1250MHz$, SEL = HIGH, $V_{SW} = 0.5V$ | 1.5 to 3.6 | | -35 | | dB |
| I_{LOSS} | Insertion Loss ⁽¹⁾ | $R_L = 50\Omega$, $C_L = 0pF$, $f = 1250MHz$, $V_{SW} = 0.5V$ | 1.5 to 3.6 | | -0.7 | | dB |
| BW | -3db Bandwidth ⁽¹⁾ | $R_L = 50\Omega$, $C_L = 0pF$, $V_{SW} = 0.5V$ | 1.5 to 3.6 | 5 | 6 | | GHz |

Note:

1. Guaranteed by characterization.

High-Speed-Related AC Electrical Characteristics

| Symbol | Description | Test Conditions | V _{CC} (V) | T _A = -40°C to +85°C | | | Units |
|--------------------|--|--|---------------------|---------------------------------|------|------|-------|
| | | | | Min. | Typ. | Max. | |
| t _{SK(P)} | D-PHY HS Mode Skew of Opposite Transitions of the Same Output ⁽¹⁾ | R _L = 50Ω, C _L = 0pF, V _{SW} = 0.3V | 1.5 to 3.6 | | 4 | 8 | ps |
| | C-PHY HS Mode Skew of 3 channels in same lane | R _L = 50Ω, C _L = 0pF, V _{SW} = 0.5V | 1.5 to 3.6 | | 4 | | |
| | D-PHY HS Mode Skew of all group A or group B channels ⁽¹⁾ | R _L = 50Ω, C _L = 0pF, V _{SW} = 0.3V | 1.5 to 3.6 | | 6 | 10 | |

Note:

1. Guaranteed by characterization.

Capacitance

| Symbol | Description | Test Conditions | T _A = -40°C to +85°C | | | Units |
|------------------|--|--|---------------------------------|------|------|-------|
| | | | Min. | Typ. | Max. | |
| C _{IN} | Control Pin Input Capacitance ⁽¹⁾ | V _{CC} = 0V, f = 1MHz | | 2.1 | | pF |
| C _{ON} | On Capacitance ⁽¹⁾ | V _{CC} = 3.3V, \overline{OE} = 0V, f = 1250MHz (In HS common value) | | 1.3 | | pF |
| C _{OFF} | Off Capacitance ⁽¹⁾ | V _{CC} or \overline{OE} = 3.3V, f = 1250MHz (Both sides in HS common value) | | 0.8 | | pF |

Note:

1. Guaranteed by characterization.

PI3WVR626

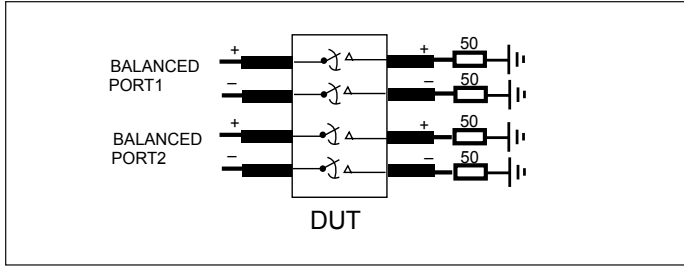


Figure 1. Crosstalk Setup

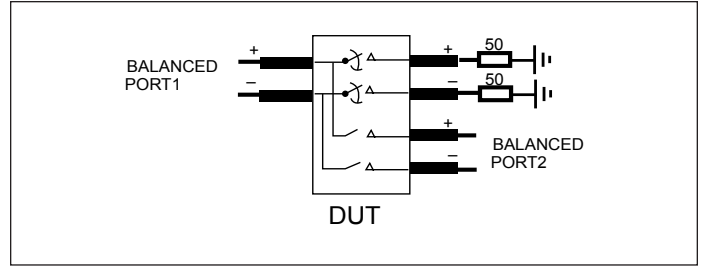


Figure 2. Off-Isolation Setup

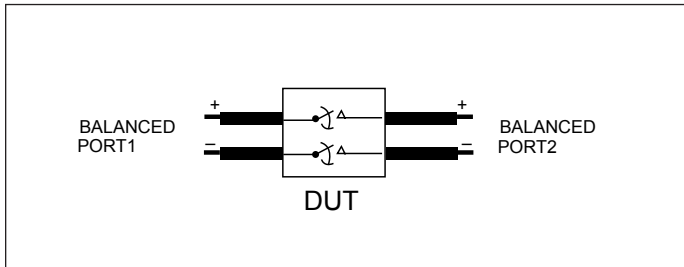


Figure 3. Differential Insertion Loss

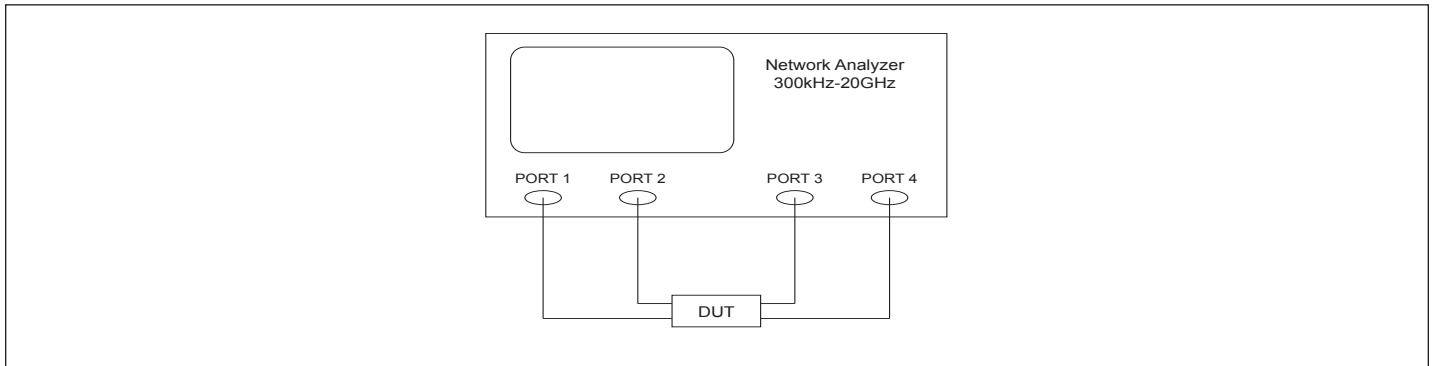
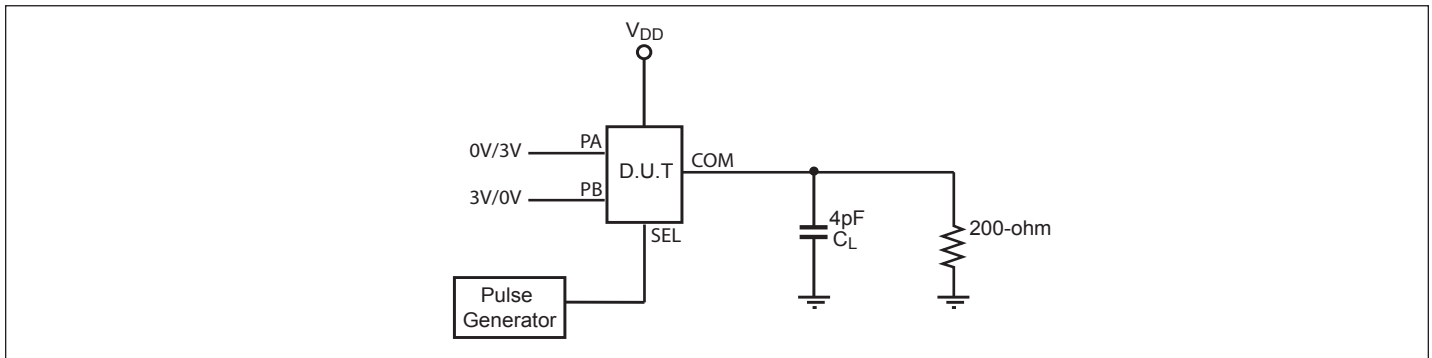


Figure 4. Test Circuit for Dynamic Electrical Characteristics

Test Circuit for Electrical Characteristics



Notes:

1. C_L = Load capacitance: includes jig and probe capacitance.
2. R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator
3. All input impulses are supplied by generators having the following characteristics: $PRR \leq \text{MHz}$, $Z_O = 50\Omega$, $t_R \leq 2.5\text{ns}$, $t_F \leq 2.5\text{ns}$.
4. The outputs are measured one at a time with one transition per measurement.

Switching Waveforms

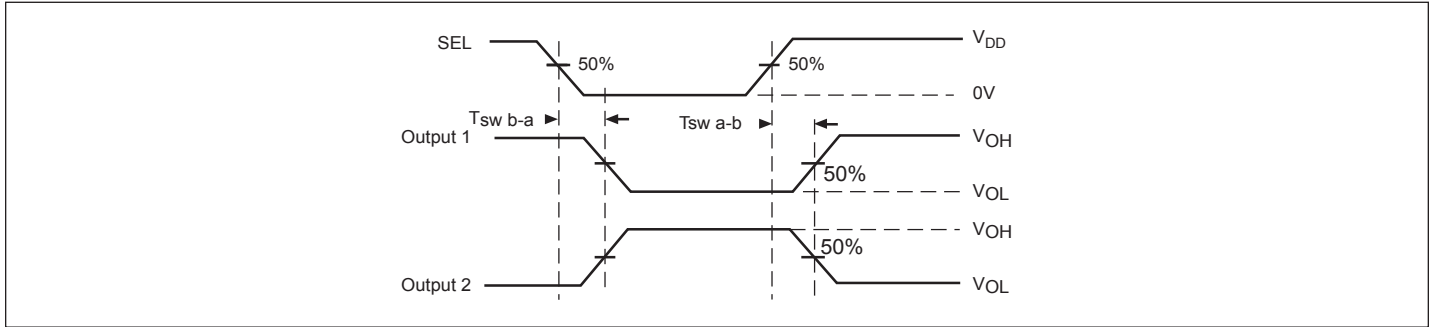


Figure 5. Voltage Waveforms for Select Timing

Test Condition

| Output 1 Test Condition | Output 2 Test Condition |
|-------------------------|-------------------------|
| PA = Low | PA = High |
| PB = High | PB = Low |

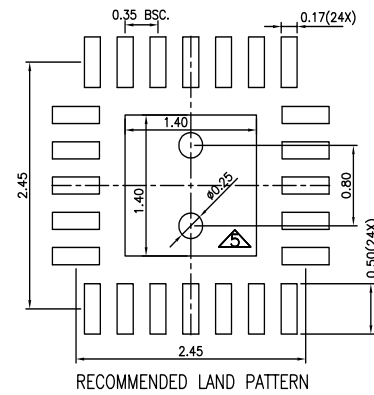
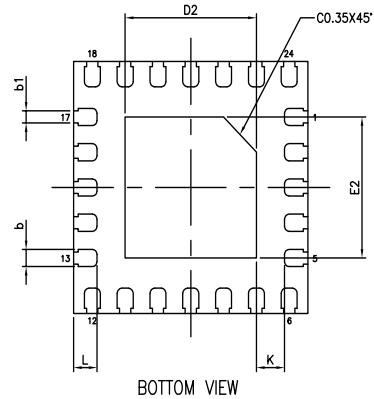
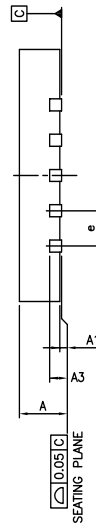
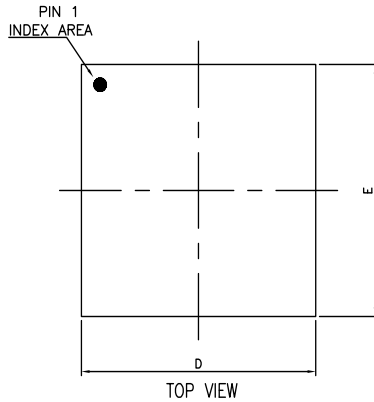
Part Marking

WVR62
6XEBE
YWX \bar{X}
o

Y: Shortened Date Code (Year)
 W: Shortened Date Code (Workweek)
 1st X: Assembly Code
 2nd X: Fab Code

Packaging Mechanical

24-X1QFN (XEB)



| SYMBOLS | MIN. | NOM. | MAX. |
|---------|------------|------|------|
| A | 0.40 | 0.45 | 0.50 |
| A1 | 0.00 | 0.02 | 0.05 |
| A3 | 0.127 REF. | | |
| b | 0.12 | 0.17 | 0.22 |
| b1 | 0.07 | 0.12 | 0.17 |
| D | 2.45 | 2.50 | 2.55 |
| E | 2.45 | 2.50 | 2.55 |
| e | 0.35 BSC | | |
| L | 0.20 | 0.25 | 0.30 |
| K | 0.20 | — | — |
| D2 | 1.35 | 1.40 | 1.45 |
| E2 | 1.35 | 1.40 | 1.45 |

NOTE :

1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
2. COPLANARITY APPLIES TO THE EXPOSED THERMAL PAD AS WELL AS THE TERMINALS.
3. REFER JEDEC MO-288
4. RECOMMENDED LAND PATTERN IS FOR REFERENCE ONLY.
5. THERMAL PAD SOLDERING AREA

| | | |
|---|-------------|----------------|
| | | DATE: 06/26/19 |
| DESCRIPTION: 24-Contact, Extra Thin Fine Pitch QFN, X1QFN | | |
| PACKAGE CODE: XEB (XEB24) | | |
| DOCUMENT CONTROL #: PD-2243 | REVISION: — | |

20-0457

For latest package info.

please check: <http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/>

Ordering Information

| Ordering Code | Package Code | Package Description |
|----------------|--------------|---|
| PI3WVR626XEBEX | XEB | 24-Contact, Extra Thin Fine Pitch (X1QFN) QFN |

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. E = Pb-free and Green
5. X suffix = Tape/Reel

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